

Automotive Dual N-Channel 250 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	250			
$R_{DS(on)}$ (Ω) at $V_{GS} = 10 \text{ V}$	0.350			
I _D (A)	7			
Configuration	Single			



FEATURES

- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualifiedd
- 100 % R_g and UIS Tested
- Material categorization:
 For definitions of compliance please see



ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD07N25-350H-GE3			

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	250	V	
Gate-Source Voltage		V _{GS}	± 30		
Continuous Drain Current	T _C = 25 °C	1	7		
	T _C = 125 °C	l _D	4		
Continuous Source Current (Diode Conduction) ^a		I _S	50	Α	
Pulsed Drain Current ^b		I _{DM}	15		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	7		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	2.4	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	- P _D	71	W	
	T _C = 125 °C		23	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient F	PCB Mount ^c	R_{thJA}	50	°C/W	
Junction-to-Case (Drain)		R _{thJC}	2.1	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							•
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		250	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		3.0	3.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 30 \text{ V}$		-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 250 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 250 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 250 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	10	-	-	Α
		V _{GS} = 10 V	I _D = 10 A	-	0.290	0.350	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 10 A, T _J = 125 °C	-	-	0.858	Ω
		V _{GS} = 10 V	I _D = 10 A, T _J = 175 °C	-	-	1.250	
Forward Transconductanceb	9 _{fs}	V _{DS}	V _{DS} = 15 V, I _D = 10 A		20	-	S
Dynamic ^b	•						
Input Capacitance	C _{iss}			-	964	1205	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	88	110	pF
Reverse Transfer Capacitance	C _{rss}			-	32	40	
Total Gate Charge ^c	Qg			-	19	29	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 125 \text{ V}, I_{D} = 10 \text{ A}$	-	6.5	-	nC
Gate-Drain Charge ^c	Q _{gd}]		-	5	-	
Gate Resistance	R_{g}	f = 1 MHz		0.98	1.97	3.00	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	9	14	
Rise Time ^c	t _r	$V_{DD} = 125 \text{ V}, \text{ R}_L = 12.5 \Omega$ $I_D \cong 10 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	8	12	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	15	23	
Fall Time ^c	t _f			-	4	6	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	15	Α
Forward Voltage	V _{SD}	I _F = 20 A, V _{GS} = 0 V		-	0.9	1.5	V

Notes

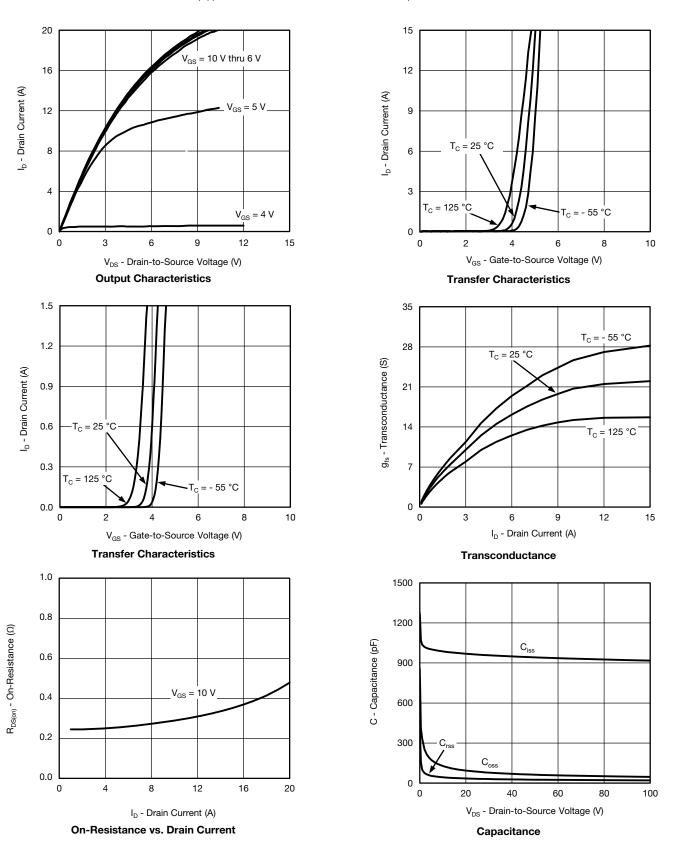
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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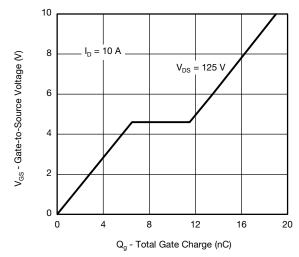
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



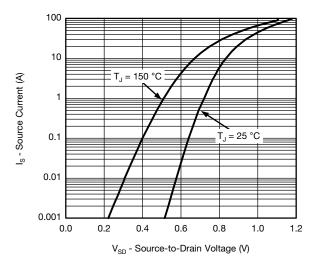


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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



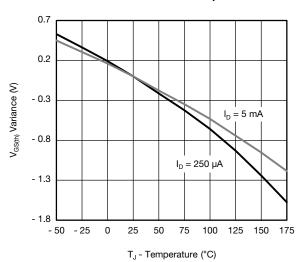
Gate Charge



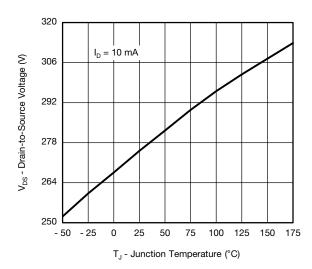
Source Drain Diode Forward Voltage

3.6 3.0 | Open control of the contr

On-Resistance vs. Junction Temperature



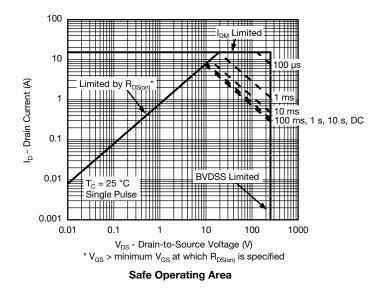
Threshold Voltage

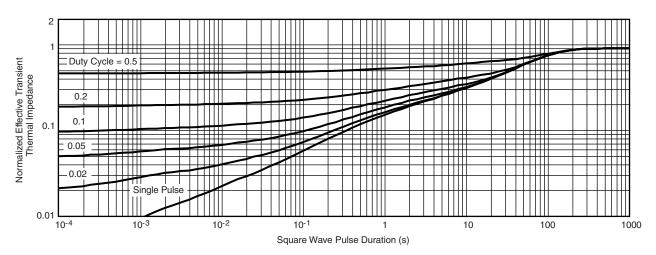


Drain Source Breakdown vs. Junction Temperature

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)

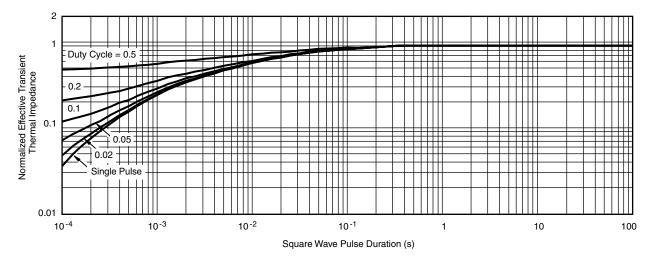




Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

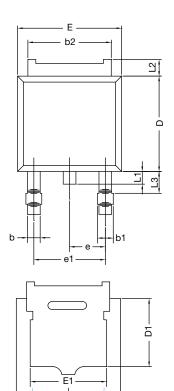
Note

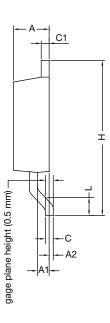
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



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TO-252AA CASE OUTLINE





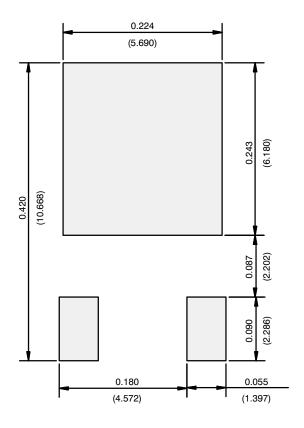
	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28 BSC		0.090 BSC		
e1	4.57 BSC		0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

Note

• Dimension L3 is for reference only.

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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